

# BUK9606-55A

N-channel TrenchMOS logic level FET Rev. 04 — 31 May 2010

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

## **1.3 Applications**

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating



## 1.4 Quick reference data

Quick reference data							
Parameter	Conditions		Min	Тур	Max	Unit	
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V	
drain current	V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	75	A	
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W	
aracteristics							
drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	4.8	5.8	mΩ	
resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$		-	-	6.7	mΩ	
	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>		-	5.3	6.3	mΩ	
e ruggedness							
non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 5  \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	1.1	J	
	Parameter         drain-source         voltage         drain current         total power         dissipation         aracteristics         drain-source         on-state         resistance	ParameterConditionsdrain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ drain current $V_{GS} = 5 \text{ V}; T_j = 25 \text{ °C};$ see Figure 3; see Figure 1total power dissipation $T_{mb} = 25 \text{ °C};$ see Figure 2drain-source on-state resistance $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ drain-source on-state resistance $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12; see Figure 13e ruggednessnon-repetitive drain-source $I_D = 75 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \text{ Q}; V_{GS} = 5 \text{ V};$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source & T_j \ge 25 \ ^{\circ}C; \ T_j \le 175 \ ^{\circ}C & \\ \hline voltage & \\ \hline drain current & V_{GS} = 5 \ ^{\circ}V; \ T_j = 25 \ ^{\circ}C; & [1] & \\ \hline see \ Figure \ 3; see \ Figure \ 1 & \\ \hline total power & \\ \hline drain-surce & \\ \hline drain-source & \\ on-state & \\ resistance & \\ \hline \hline V_{GS} = 10 \ ^{\circ}V; \ ^{\circ}I_D = 25 \ ^{\circ}C; & \\ \hline V_{GS} = 4.5 \ ^{\circ}V; \ ^{\circ}I_D = 25 \ ^{\circ}C; & \\ \hline V_{GS} = 5 \ ^{\circ}V; \ ^{\circ}I_D = 25 \ ^{\circ}C; & \\ \hline V_{GS} = 5 \ ^{\circ}V; \ ^{\circ}I_D = 25 \ ^{\circ}C; & \\ \hline V_{GS} = 5 \ ^{\circ}V; \ ^{\circ}I_D = 25 \ ^{\circ}C; & \\ \hline see \ Figure \ 12; \ see \ Figure \ 13 & \\ \hline e \ ruggedness & \\ \hline non-repetitive & I_D = 75 \ ^{\circ}A; \ V_{GS} = 5 \ ^{\circ}V; & \\ \hline R_{GS} = 50 \ ^{\circ}Q; \ V_{GS} = 5 \ ^{\circ}V; & \\ \hline \end{array}$	$\begin{tabular}{ c c c c c } \hline Parameter & Conditions & Min \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C & - \\ \hline voltage & & & & & & & \\ \hline drain current & V_{GS} = 5 \ V; \ T_j = 25 \ ^\circ C; & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & & & & & \\ \hline total power & & $	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C$ drain current $V_{GS} = 5 \ V; \ T_j = 25 \ ^\circ C;$ [1]total power dissipation $T_{mb} = 25 \ ^\circ C;$ see Figure 2total power dissipation $T_{mb} = 25 \ ^\circ C;$ see Figure 2aracteristics $V_{GS} = 10 \ V; \ I_D = 25 \ A;$ -4.8drain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 25 \ A;$ $V_{GS} = 4.5 \ V; \ I_D = 25 \ A;$ $V_{GS} = 5 \ V; \ I_D = 25 \ A;$ 5.3 $T_j = 25 \ ^\circ C;$ see Figure 12; see Figure 13-5.3e ruggednessI_D = 75 \ A; \ V_{sup} \le 55 \ V; $R_{GS} = 50 \ \Omega; \ V_{GS} = 5 \ V;$	Parameter         Conditions         Min         Typ         Max           drain-source voltage $T_j \ge 25 ^\circ$ C; $T_j \le 175 ^\circ$ C         -         -         55           drain current $V_{GS} = 5 ^\circ$ Y; $T_j = 25 ^\circ$ C;         [1]         -         -         75           total power dissipation $T_{mb} = 25 ^\circ$ C; see Figure 1         -         -         300           aracteristics         V_{GS} = 10 V; I_D = 25 A; $T_j = 25 ^\circ$ C         -         4.8         5.8           drain-source on-state resistance $V_{GS} = 10 ^\circ$ Y; I_D = 25 A; $T_j = 25 ^\circ$ C         -         -         6.7 $V_{GS} = 4.5 ^\circ$ Y; I_D = 25 A; $T_j = 25 ^\circ$ C         -         -         6.7 $V_{GS} = 5 ^\circ$ Y; I_D = 25 A; $T_j = 25 ^\circ$ C         -         -         5.3         6.3           eruggedness         I_D = 75 A; V_{sup} \le 55 V; R_{GS} = 5 V; I_S = 5 V;         -         -         1.1	

[1] Continuous current is limited by package.

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT404 (D2PAK)

# 3. Ordering information

Table 3. Order	ing information		
Type number	Package		
	Name	Description	Version
BUK9606-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

BUK9606-55A Product data sheet

# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

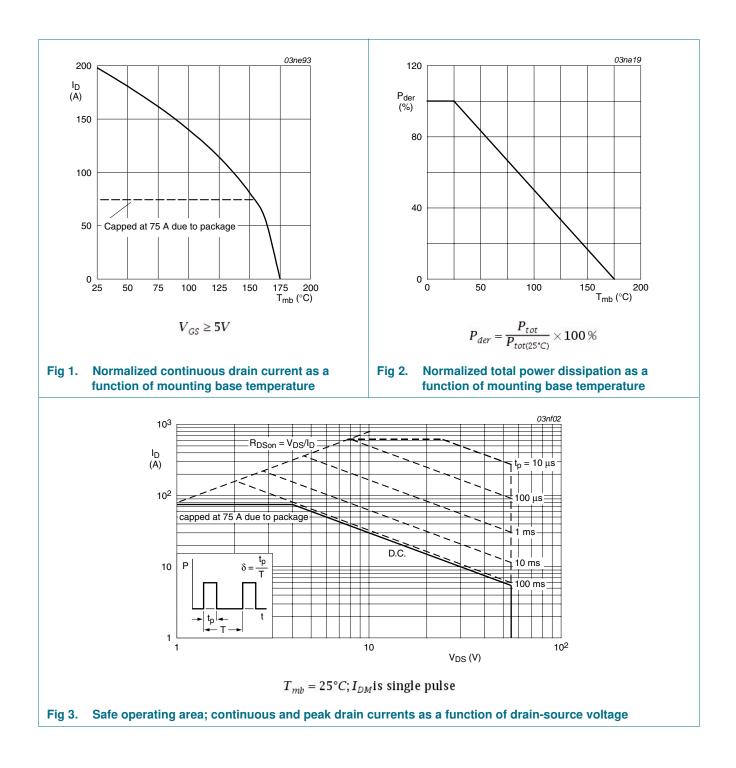
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V <sub>GS</sub>	gate-source voltage			-15	-	15	V
I <sub>D</sub>	drain current	$V_{GS} = 5 V; T_j = 25 °C;$	<u>[1]</u>	-	-	154	А
		see <u>Figure 3</u> ; see <u>Figure 1</u>	[2]	-	-	75	А
		$V_{GS}$ = 5 V; $T_j$ = 100 °C; see <u>Figure 1</u>	[2]	-	-	75	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; t <sub>p</sub> ≤ 10 μs; pulsed; see <u>Figure 3</u>		-	-	616	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drai	n diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	-	154	А
			[2]	-	-	75	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	616	А
Avalanche r	uggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(\text{init})} = 25 \ ^\circ\text{C}; \ \text{unclamped} \end{array}$		-	-	1.1	J

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

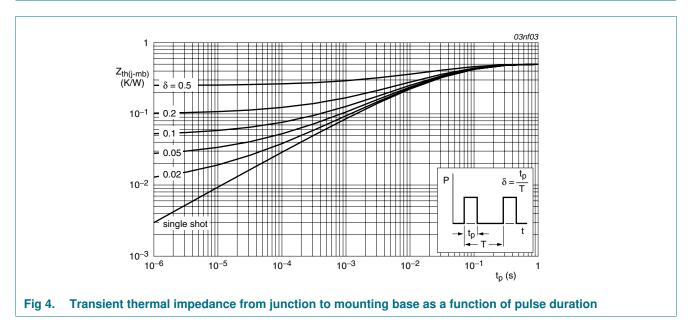
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## 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on a printed-circuit board ; minimum footprint	-	50	-	K/W

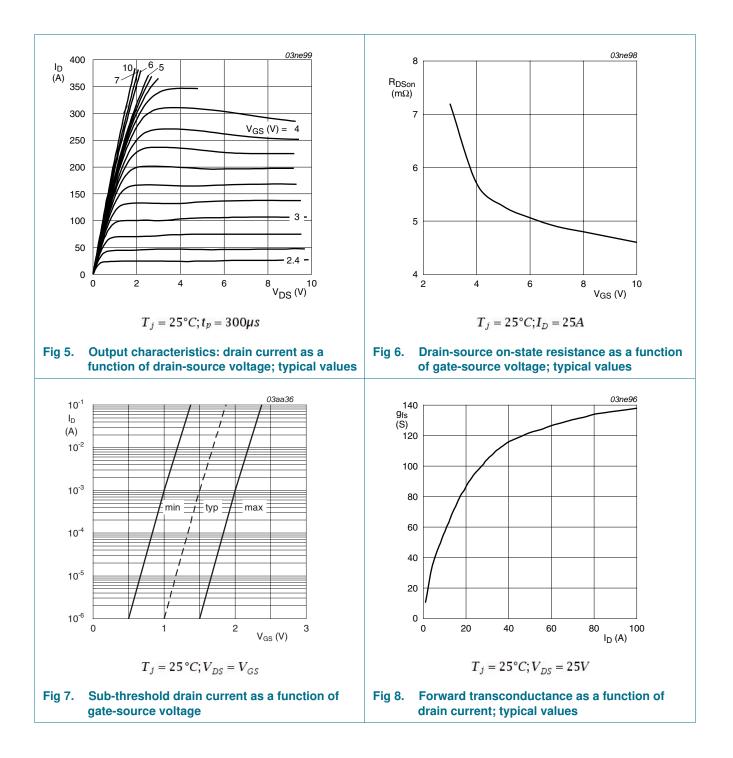


# 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	1	1.5	2	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 11</u>	-	-	2.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -10 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	13.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	4.8	5.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	6.7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	5.3	6.3	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	6500	8600	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{14}$	-	1000	1200	pF
C <sub>rss</sub>	reverse transfer capacitance		-	650	850	рF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	45	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	180	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	420	-	ns
t <sub>f</sub>	fall time		-	235	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_{j}$ = 25 $^{\circ}\text{C}$	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 30 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s};$	-	80	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	200	-	nC

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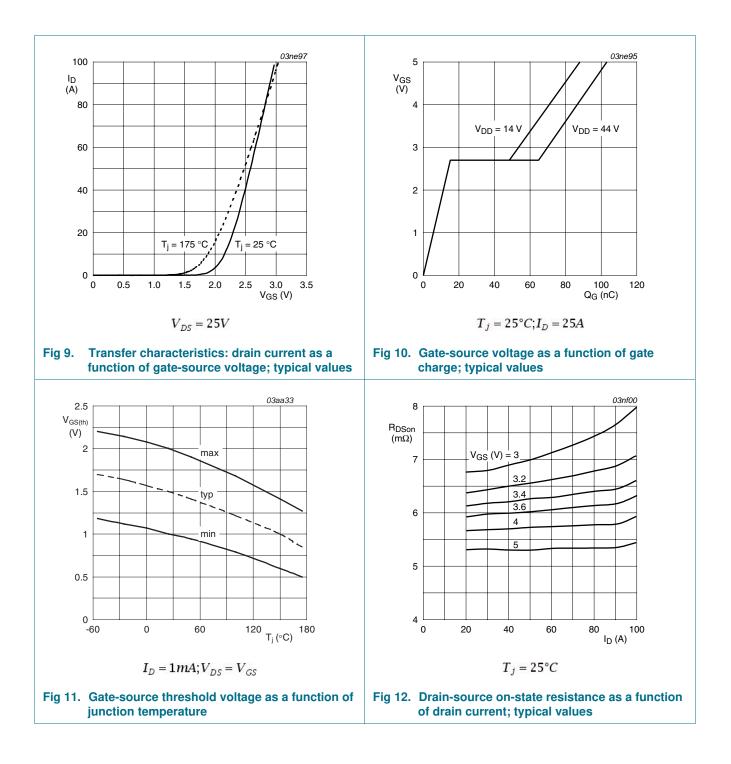
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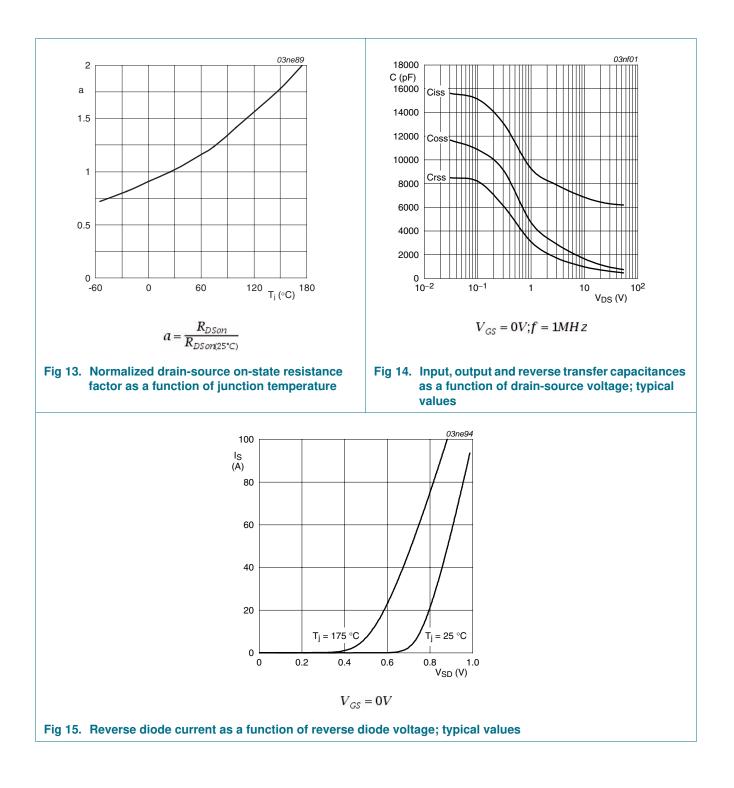
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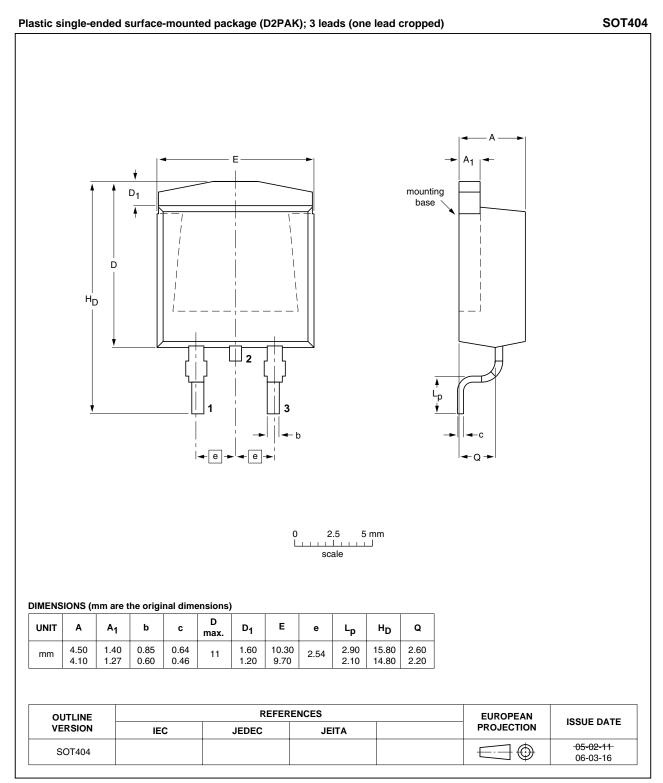
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# 7. Package outline



#### Fig 16. Package outline SOT404 (D2PAK)

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# 8. Revision history

Table 7.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9606-55A v.4	20100531	Product data sheet	-	BUK9506_9606_9E06_55A-03
Modifications:		at of this data sheet ha	•	ed to comply with the new identity
	<ul> <li>Legal text</li> </ul>	s have been adapted	to the new compa	any name where appropriate.
	• •	ber BUK9606-55A se _9606_9E06_55A-03	•	sheet
BUK9506_9606_9E06_55A-03 (9397 750 08416)	20010723	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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